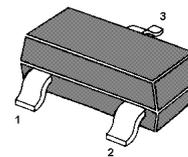


BCV26 / BCV46

PNP Darlington Transistors

for preamplifier input applications



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	BCV26 BCV46	- V_{CBO}	40 80	V
Collector Emitter Voltage	BCV26 BCV46	- V_{CEO}	30 60	V
Emitter Base Voltage		- V_{EBO}	10	V
Collector Current		- I_C	500	mA
Peak Collector Current		- I_{CM}	800	mA
Base Current		- I_B	100	mA
Total Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{Stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

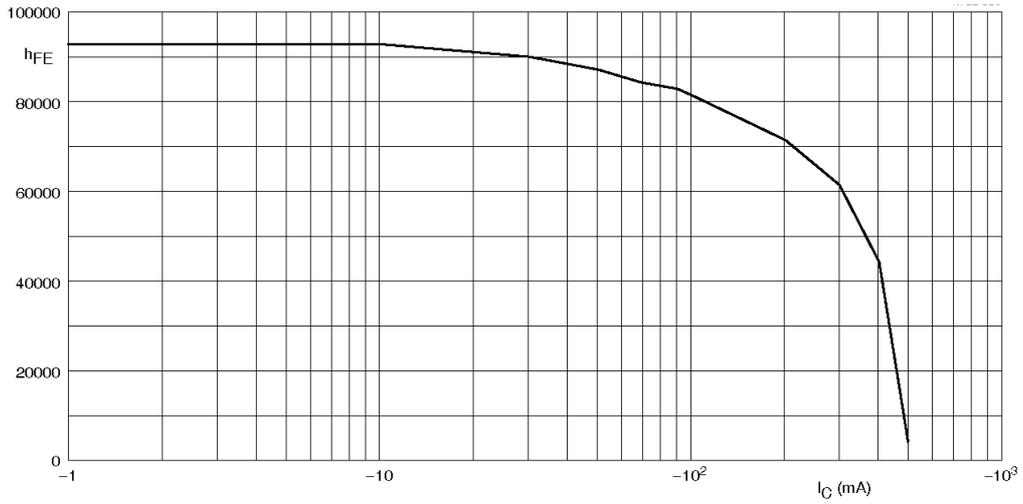
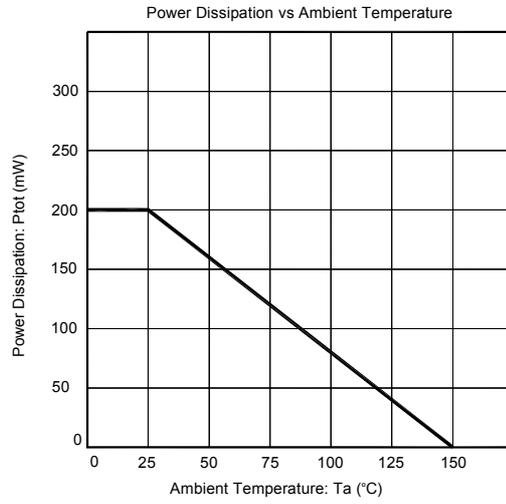
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$	BCV26 BCV46	h_{FE}	4000 2000	- -	- -
at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	BCV26 BCV46	h_{FE}	10000 4000	- -	- -
at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$	BCV26 BCV46	h_{FE}	20000 10000	- -	- -
Collector Base Cutoff Current					
at $-V_{CB} = 30\text{ V}$	BCV26	- I_{CBO}	-	100	nA
at $-V_{CB} = 60\text{ V}$	BCV46		-	100	
Emitter Base Cutoff Current					
at $-V_{EB} = 10\text{ V}$		- I_{EBO}	-	100	nA
Collector Base Breakdown Voltage	BCV26 BCV46	- $V_{(BR)CBO}$	40 80	- -	V
Collector Emitter Breakdown Voltage	BCV26 BCV46	- $V_{(BR)CEO}$	30 60	- -	V
Emitter Base Breakdown Voltage		- $V_{(BR)EBO}$	10	-	V
Collector Emitter Saturation Voltage		- $V_{CE(sat)}$	-	1	V
Base Emitter Saturation Voltage		- $V_{BE(sat)}$	-	1.5	V
Base Emitter On-state Voltage		- $V_{BE(on)}$	-	1.4	V
Transition Frequency		f_T	-	220	MHz
at $-V_{CE} = 5\text{ V}$, $-I_C = 30\text{ mA}$, $f = 100\text{ MHz}$					

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
 ISO 9001 : 2008 Certificate No. 5014012
 OHSAS 18001 : 2007 Certificate No. 05131508008
 IECQ QC 080000 Certificate No. E5011000114122

Dated : 18/08/2012



$V_{CE} = -2V$.

DC current gain; typical values.